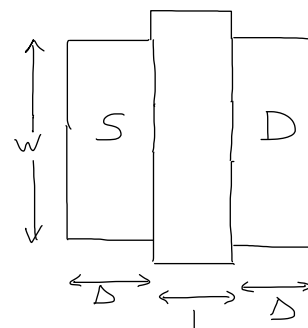


\* Summary of Mosfet parasitic capacitors:

|                     | $C_{gse}=C_{gde}$             | $C_{gb}$                       | $C_{gsi}$                      | $C_{gdi}$                      | $C_{sbi}$                         | $C_{dbi}$                         |
|---------------------|-------------------------------|--------------------------------|--------------------------------|--------------------------------|-----------------------------------|-----------------------------------|
| cutoff              | $C_{ox} \cdot W \cdot L_{ov}$ | $C_{ox} \cdot W \cdot L_{eff}$ | $\emptyset$                    | $\emptyset$                    | $\emptyset$                       | $\emptyset$                       |
| triode              | $C_{ox} \cdot W \cdot L_{ov}$ | $\emptyset$                    | $\frac{1}{2} C_{ox} W L_{eff}$ | $\frac{1}{2} C_{ox} W L_{eff}$ | $\frac{1}{2} C_j L_{eff} \cdot W$ | $\frac{1}{2} C_j L_{eff} \cdot W$ |
| saturation (active) | $C_{ox} \cdot W \cdot L_{ov}$ | $\emptyset$                    | $\frac{2}{3} C_{ox} W L_{eff}$ | $\frac{1}{3} C_{ox} W L_{eff}$ | $\frac{2}{3} C_j L_{eff} W$       | $\frac{1}{3} C_j L_{eff} W$       |

|                     | $C_{sbe}$                      | $C_{dbe}$                      |
|---------------------|--------------------------------|--------------------------------|
| cutoff              | $A_s C_j + P_s C_{jsw}$        | $A_d C_j + P_d C_{jsw}$        |
| triode              | $A_s \cdot C_j + P'_s C_{jsw}$ | $A_d C_j + P'_d C_{jsw}$       |
| saturation (active) | $A_s \cdot C_j + P'_s C_{jsw}$ | $A_d \cdot C_j + P'_d C_{jsw}$ |

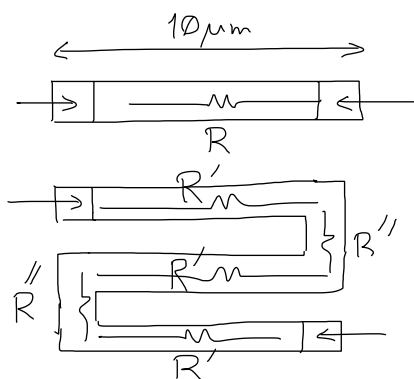


$$C_{ox} \left[ \frac{F}{m^2} \right], C_j \left[ \frac{F}{m^2} \right], C_{jsw} \left[ \frac{F}{m} \right] \quad A_s = \Delta \cdot W, P_s = 2(\Delta + W), P'_s = 2\Delta + W$$

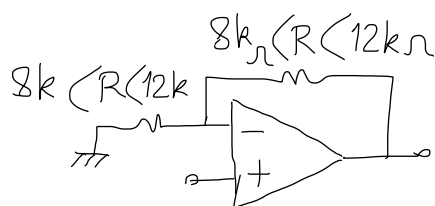
$$A_d = \Delta \cdot W, P_d = 2(\Delta + W), P'_d = 2\Delta + W$$

$$C_j = \frac{C_{j0} \left[ \frac{F}{m^2} \right]}{\left( 1 + \frac{V_r}{\phi_0} \right)^n}, \quad C_{jsw} = \frac{C_{jsw0} \left[ \frac{F}{m} \right]}{\left( 1 + \frac{V_r}{n} \right)^n}$$

$C_{jsw} \approx C_j \cdot X_j$   
junction depth



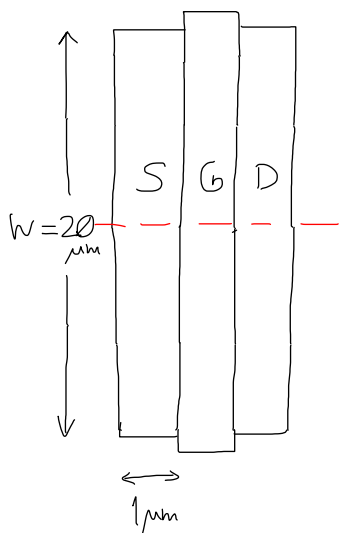
$$3R' + 2R'' = 3R$$



Tolerance of on-chip resistors is 20%  
(ideally  $R = 10k\Omega$ )

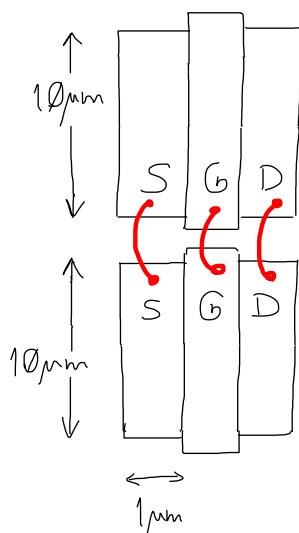
\* interdigitated layout minimizes mismatch

\* layout :



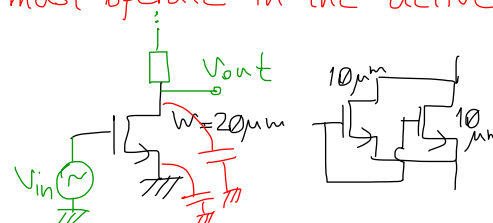
$$A_s = 20\mu\text{m} \times 1\mu\text{m} = A_d$$

$$P_s = 20\mu + 1\mu + 1\mu = P_d$$

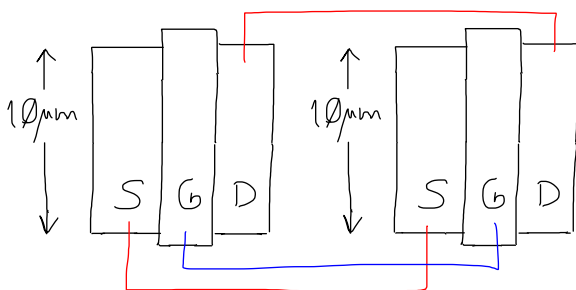


$$A_s = (10\mu\text{m} \times 1\mu\text{m}) + (10\mu\text{m} \times 1\mu\text{m}) = A_d$$

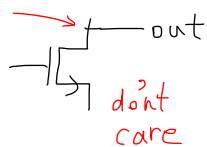
$$P_s = (10\mu + 1\mu + 1\mu) + (10\mu + 1\mu + 1\mu) = P_d$$



this will be a transistor with 20 μm width



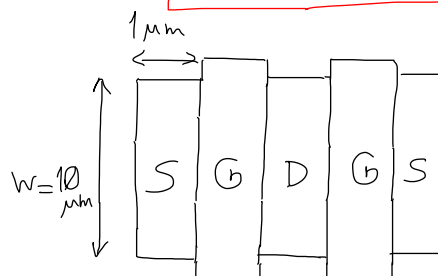
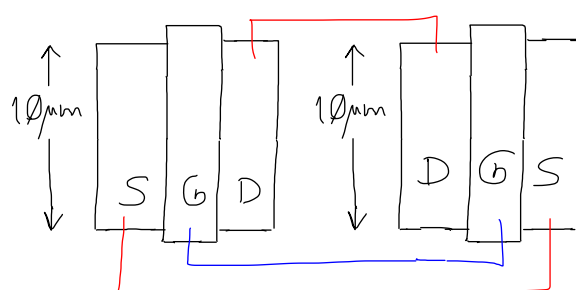
critical node



\* Always use interdigitated multiple finger layout

$$P_s = (10\mu + 1\mu + 1\mu) \times 2$$

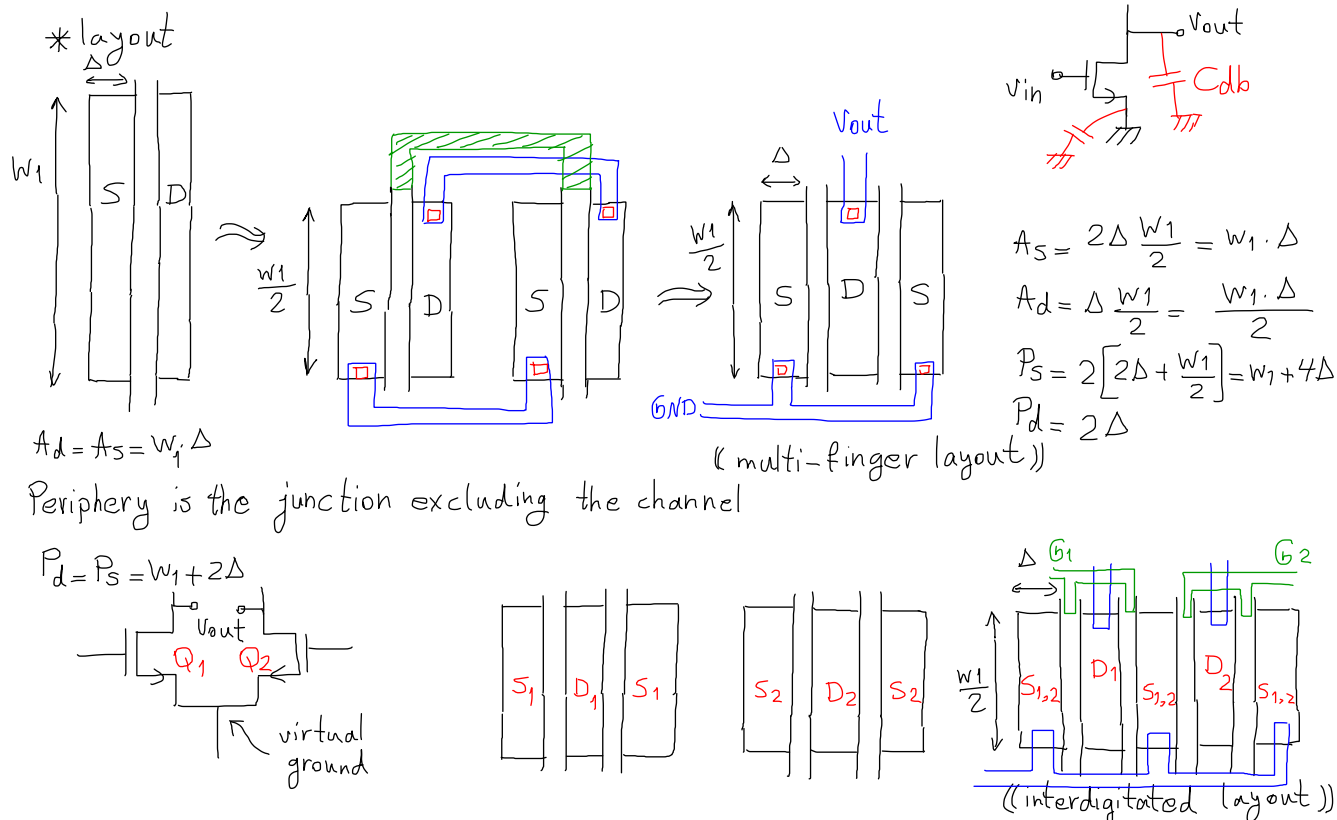
$$P_d = 1\mu + 1\mu$$



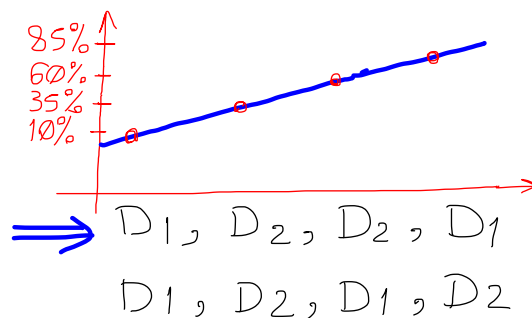
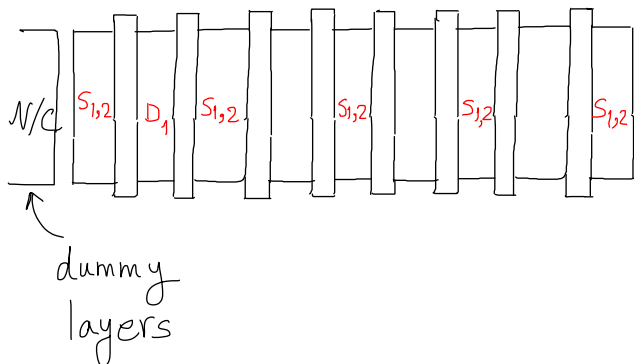
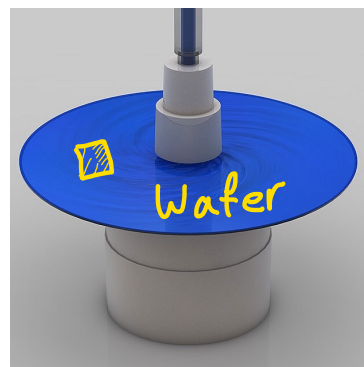
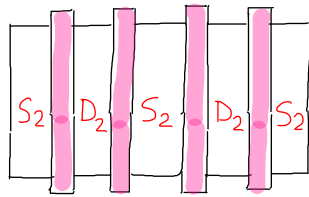
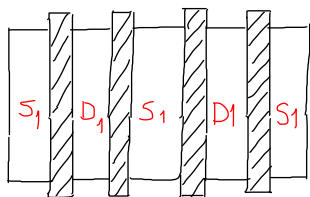
$$W = 2 \text{ fingers} \times 10\mu\text{m} = 20\mu\text{m}$$

$$A_s = 10\mu\text{m} \times 1\mu\text{m} \times 2$$

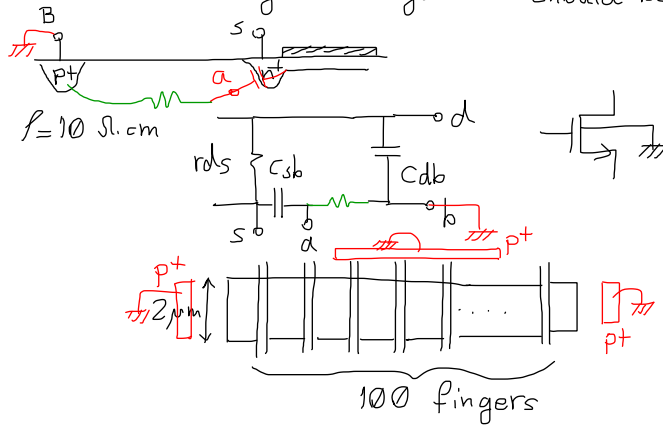
$$A_d = 10\mu\text{m} \times 1\mu\text{m}$$



\* Example of interdigitated layout with  $Q_1$  and  $Q_2$  designed using 4 fingers



\* Bulk rule : the minimum distance between bulk to any source junction should be less than  $10\mu\text{m}$



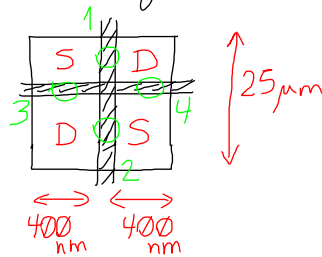
$$A_s = 3 \frac{w_1}{2} \Delta$$

$$A_{d1} = \frac{w_1}{2} \Delta = A_{d2}$$

$$P_s = 2 \left[ 2\Delta + \frac{w_1}{2} \right] + 2\Delta$$

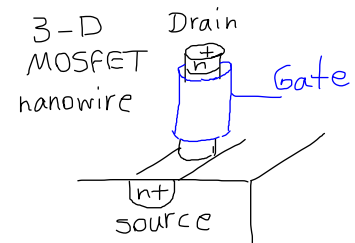
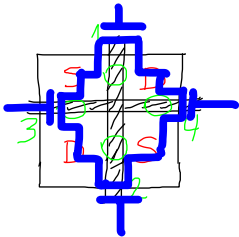
$$P_{d1} = 2\Delta = P_{d2}$$

Waffle layout:



$$A_D = A_S = 2 \times \frac{25\mu\text{m}}{2} \times 400\text{nm}$$

$$P_D = P_S = 2 \left[ 400\text{nm} + \frac{25\mu\text{m}}{2} \right]$$



Also look at FinFets